

# MICRO ELECTRONICS

2N5225

NPN  
SILICON  
TRANSISTOR

## DESCRIPTION

2N5225 is NPN silicon planar transistor use in general purpose consumer and industrial amplifier and switching applications.

CASE TO-92A



EBC

## ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	$V_{CBO}$	25V
Collector-Emitter Voltage	$V_{CEO}$	25V
Emitter-Base Voltage	$V_{EBO}$	4V
Collector Current	$I_C$	200mA
Continuous Power Dissipation	$P_d$	350mW
Operating & Storage Junction Temperature	$T_j, T_{stg}$	-55 to +150°C

## ELECTRO-OPTICAL CHARACTERISTICS

( $T_a = 25^\circ C$ )

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	$LV_{CEO}^*$	25		V	$I_C = 10mA$	$I_B = 0$
Collector-Base Breakdown Voltage	$BV_{CBO}$	25			$I_C = 0.1mA$	$I_E = 0$
Collector Cutoff Current	$I_{CBO}$		300	nA	$V_{CB} = 15V$	$I_E = 0$
Emitter Cutoff Current	$I_{EBO}$		500	nA	$V_{EB} = 4V$	$I_C = 0$
D.C. Current Gain	$H_{FE}^*$	25			$I_C = 10mA$	$V_{CE} = 10V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$		0.8	V	$I_C = 100mA$	$I_B = 10mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$		1.1	V	$I_C = 50mA$	$I_B = 2.5mA$
Output Capacitance	$C_{ob}$		20	pF	$V_{CB} = 10V$	$f = 1MHz$
Current Gain-Bandwidth Product	$f_T$	50		pF	$I_C = 20mA$	$V_{CE} = 10V$

\* Pulse test : pulse width  $< 300\mu S$ , duty cycle  $< 2\%$ .



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